

## Single P-Channel MOSFET

### DESCRIPTION

SMC2327SN is the P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced trench technology devices are well suited for high efficiency fast switching applications, low in-line power loss are needed in small outline surface mount package.

### PART NUMBER INFORMATION

**SMC 2327 SN - TR G**  
 a      b      c      d      e

- a : Company name.
- b : Product Serial number.
- c : Package code      SN: SOT-23
- d : Handling code      TR: Tape&Reel
- e : Green produce code G: *RoHS Compliant*

### FEATURES

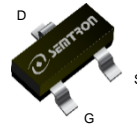
**$V_{DS}=-20V$ ,  $I_D=-4.2A$**

- $R_{DS(ON)}=38m\Omega(Typ.)@V_{GS}=-10V$
- $R_{DS(ON)}=45m\Omega(Typ.)@V_{GS}=-4.5V$
- $R_{DS(ON)}=60m\Omega(Typ.)@V_{GS}=-2.5V$
- $R_{DS(ON)}=80m\Omega(Typ.)@V_{GS}=-1.8V$

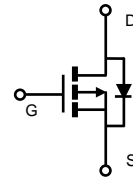
- ◆ Fast switch
- ◆ 1.8V Low gate drive applications
- ◆ High power and current handling capability

### APPLICATIONS

- ◆ Hand-Held Instruments
- ◆ Load Switch



SOT-23



### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^{\circ}C$ Unless otherwise noted )

Symbol	Parameter	Rating	Units	
$V_{DSS}$	Drain-Source Voltage	-20	V	
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V	
$I_D$	Continuous Drain Current <sup>A</sup> ( $V_{GS}=-4.5V$ )	$T_A=25^{\circ}C$	-4.2	A
		$T_A=70^{\circ}C$	-3.4	A
$I_{DM}$	Pulsed Drain Current <sup>B</sup>	16.8	A	
$P_D$	Power Dissipation <sup>A</sup>	$T_A=25^{\circ}C$	1.3	W
		$T_A=70^{\circ}C$	0.8	W
$T_J$	Operation Junction Temperature	-55/150	$^{\circ}C$	
$T_{STG}$	Storage Temperature Range	-55/150	$^{\circ}C$	

### THERMAL RESISTANCE

Symbol	Parameter	Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>A</sup>	$t \leq 10s$	95	$^{\circ}C/W$
	Thermal Resistance Junction to Ambient <sup>AC</sup>	Steady-State	130	

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C Unless otherwise noted )

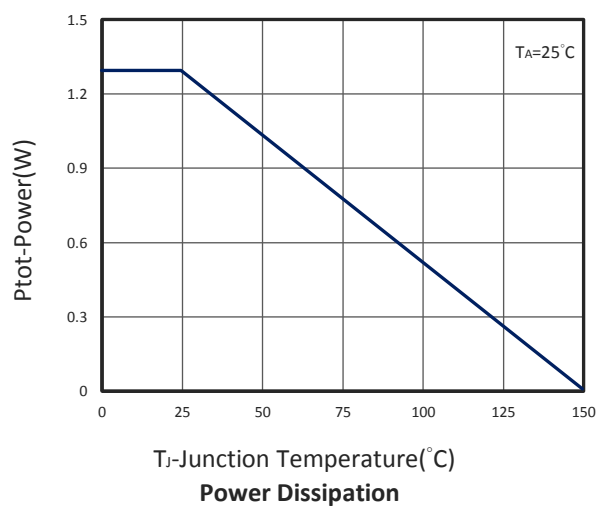
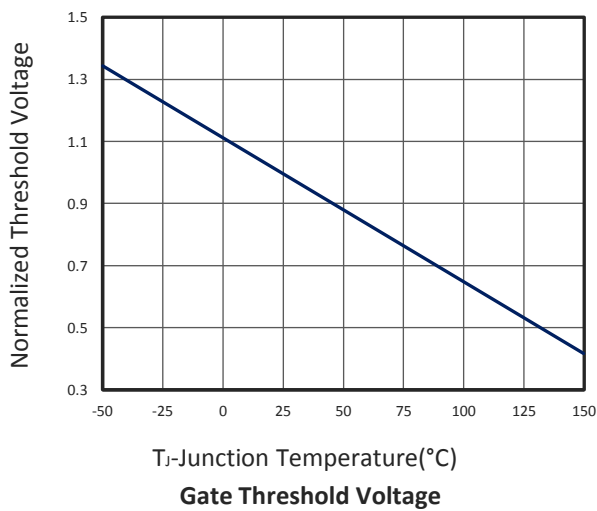
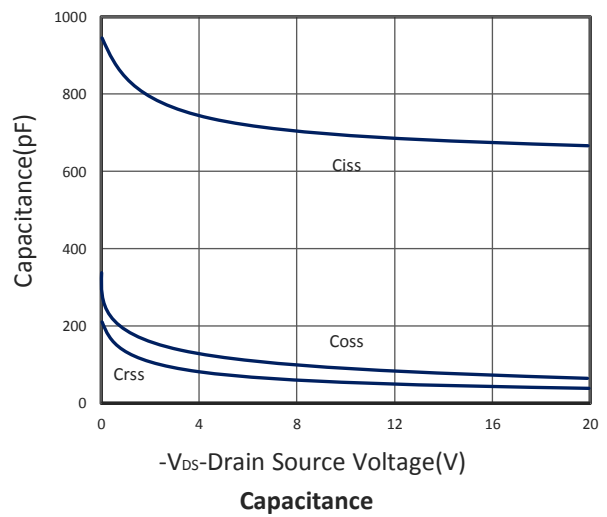
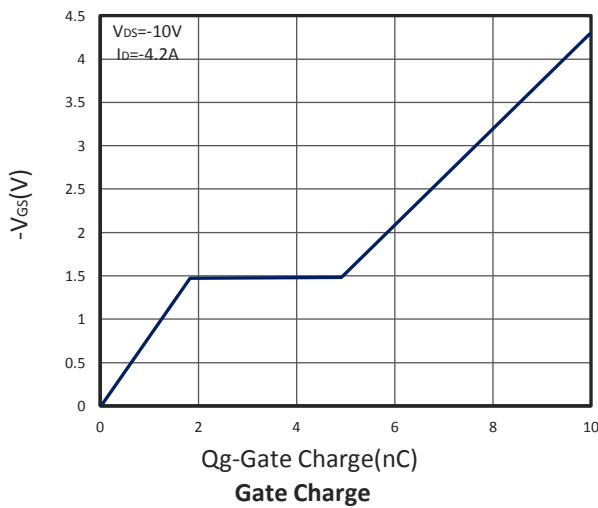
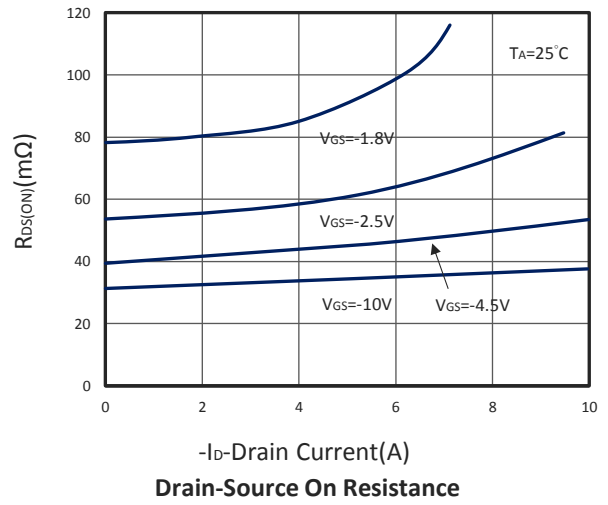
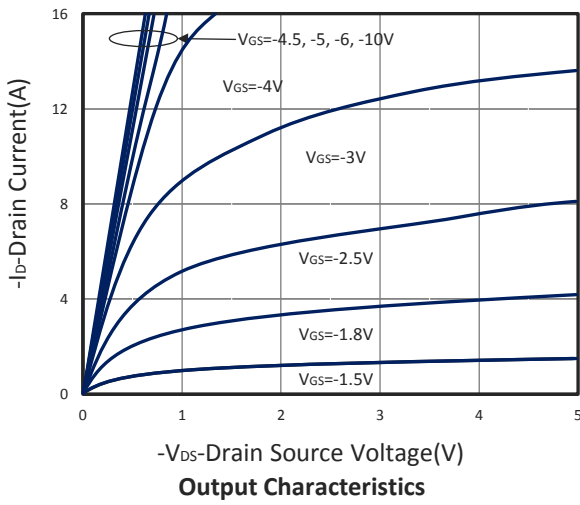
Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-20			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.5	-0.7	-1	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C			-1	μA
		V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, T <sub>J</sub> =75°C			-10	
R <sub>DS(ON)</sub>	Drain-source On-Resistance <sup>D</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.5A		38	43	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A		45	50	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.5A		60	68	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2A		80	95	
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A		12		S
<b>Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage <sup>D</sup>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V			-1	V
I <sub>S</sub>	Diode Continuous Forward Current				-2.1	A
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =-3A, di/dt=100A/μs		20		ns
Q <sub>rr</sub>	Reverse Recovery Charge			6.7		nC
<b>Dynamic and Switching Parameters <sup>E</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V I <sub>D</sub> =-4.2A		10.3	14.4	nC
Q <sub>GS</sub>	Gate-Source Charge			1.9	2.5	
Q <sub>GD</sub>	Gate-Drain Charge			3	4.2	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHz		680		pF
C <sub>oss</sub>	Output Capacitance			76		
C <sub>rss</sub>	Reverse Transfer Capacitance			45		
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =-10V, V <sub>GEN</sub> =-4.5V R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-1A		5.8	11	nS
t <sub>r</sub>				21	40	
t <sub>d(off)</sub>	Turn-Off Time			32	61	
t <sub>f</sub>				16	30	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

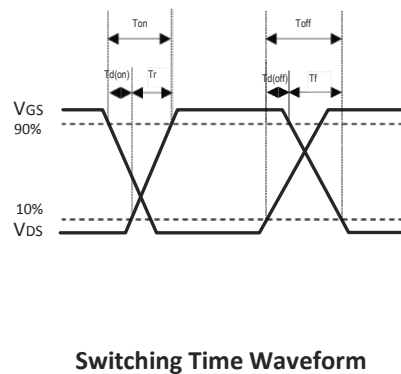
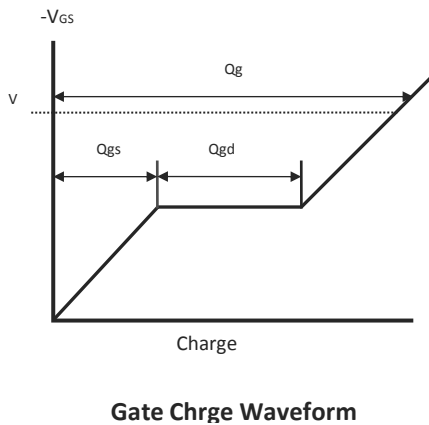
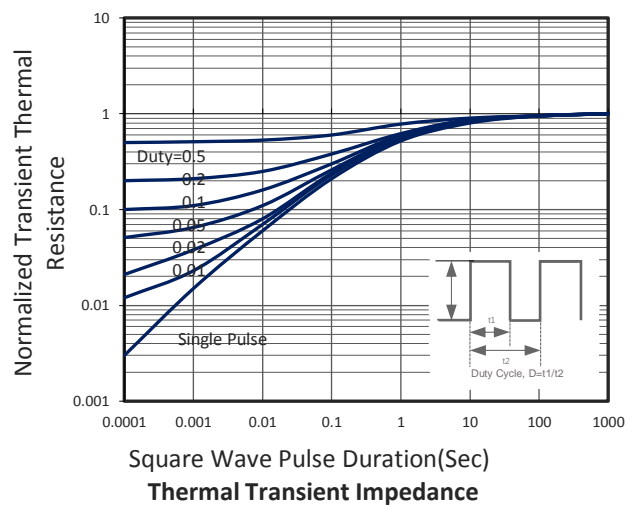
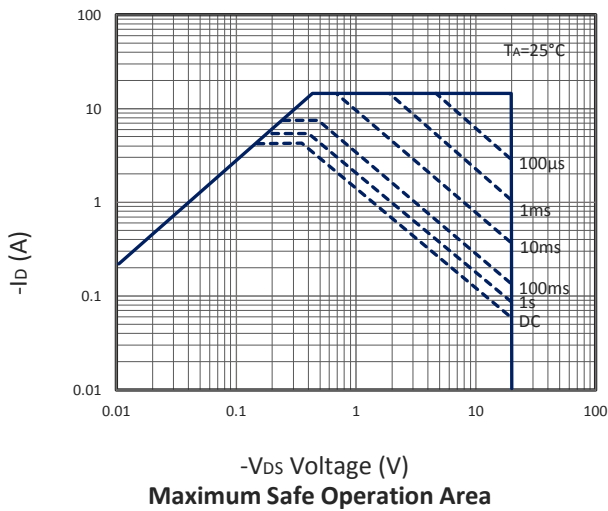
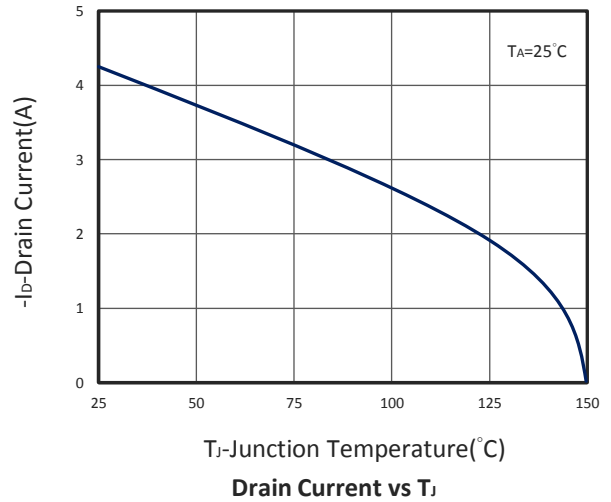
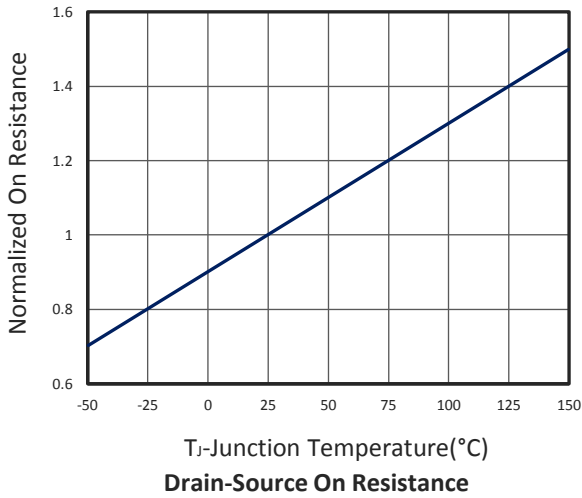
- A. Surface mounted on FR4 board using 1 in<sup>2</sup> pad size.
- B. Pulsed width limited by maximum junction temperature, T<sub>J(MAX)</sub>=150°C (initial temperature T<sub>J</sub>=25°C).
- C. Using ≤ 10s junction-to-ambient thermal resistance is base on T<sub>J(MAX)</sub>=150°C.
- D. Pulse test width ≤300μs and duty cycle ≤ 2%.
- E. Guaranteed by design, not subject to production testing.

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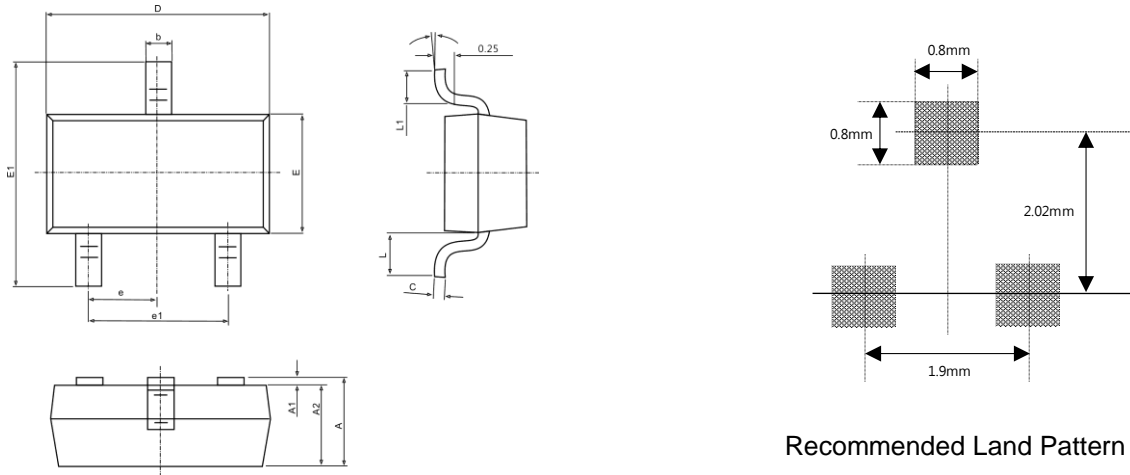
## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS



## ■ SOT-23 PACKAGE DIMENSIONS



Recommended Land Pattern

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°